

Schottky Barrier Diode

RB481K

●Applications

Low current rectification

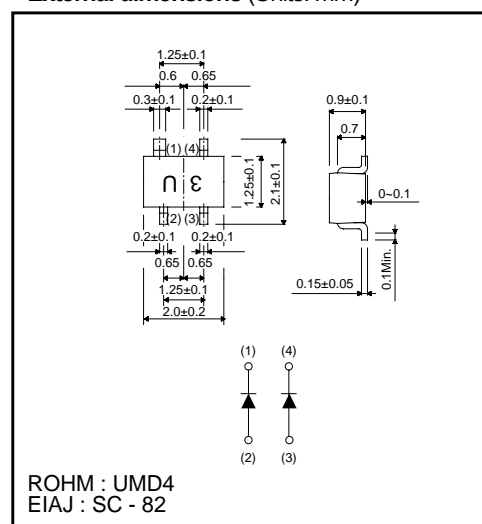
●Features

- 1) Compact size.
- 2) High reliability.
- 3) Extremely low forward voltage.
- 4) This is a composite component and is ideal for reducing the number of components used.

●Construction

Silicon epitaxial planar

●External dimensions (Units: mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	30	V
DC reverse voltage	V_R	30	V
Mean rectifying current	I_O	0.2	A
Peak forward surge current*	I_{FSM}	1	A
Junction temperature	T_J	125	°C
Storage temperature	T_{stg}	-40~+125	°C

* 60 Hz for 1 ms

●Electrical characteristics (Ta=25°C unless otherwise noted)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{F1}	—	0.18	0.28	V	$I_F=1mA$
	V_{F2}	—	0.25	0.33	V	$I_F=10mA$
	V_{F3}	—	0.34	0.43	V	$I_F=100mA$
	V_{F4}	—	0.40	0.50	V	$I_F=200mA$
Reverse current	I_R	—	3.6	30	μA	$V_R=10V$

Diodes

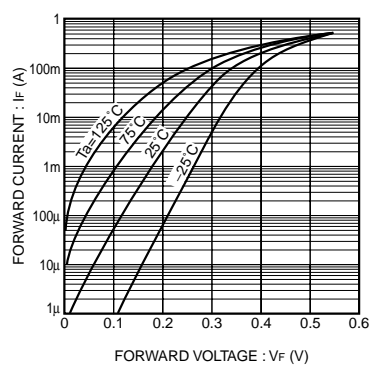
● Electrical characteristic curves ($T_a=25^\circ\text{C}$)

Fig. 1 Forward temperature characteristic

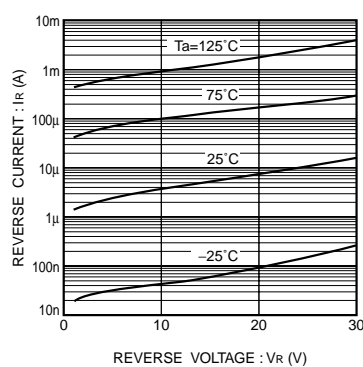


Fig. 2 Reverse temperature characteristic

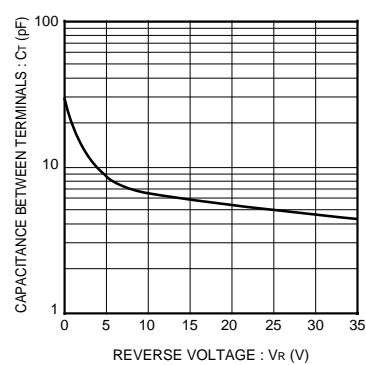


Fig. 3 Capacitance between terminals characteristic